Form PTO-1449 U.S. DEPARTMENT OF COMMERCE (REV. 8-83) PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. BU9-98-179	SERIAL NO. 09/224,759
INFORMATION DISCLOSURE CITATION	APPLICANT Furukawa et al.	
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U. S. PATENT DOCUMENTS

EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB-CLASS	FILING DATE IF APPROPRIATE

FOREIGN PATENT DOCUMENTS

	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB-CLASS	TRANSLATION YES	TRANSLATION NO

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

JAG		Stanasolovich, et al. "Method for Reducing the Diffusion Contact Borders", IBM Technical Disclosure Bulletin, Vol. 32, No. 4A, September 1989, pgs. 344-345.
JAG		Weiner et al. "Self Aligned Silicide Formation Using Gas Immersion Laser Annealing (GILA)", Ultratech Stepper technical brief, March 3, 1997.
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JAG		Derwent World Patent Index "Japanese Patent 8148680 Abstract", June 7, 1996.

EXAMINER	DATE CONSIDERED
Joanne A. Gaudia	June 2, 2001

*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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JAG		5,620,912	04/1997	Hwang et al.	—	—	
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JAG		Jasinski et al. 27341 "Photochemical Deposition of Graded Silicon Nitride", Research Disclosure, January 1987, Number 273
		Jasinski et al. 27343 "Photochemical Deposition of Silicon Nitride", Research Disclosure, January 1987, Number 273
JAG		Mihailescu et al. "Direct nitridation of a silicon surface by multipulse excimer laser irradiation in a nitrogen-containing ambient gas", Journal of Applied Physics 70, August 15, 1991, pp 2123-2131.
JAG		Mihailescu et al. "Synthesis and deposition of silicon nitride films by laser reactive ablation of silicon in low pressure ammonia: A parametric study", Journal of Vacuum Science Technology 14, July/August 1996, pp 1986-1994.

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Joannie A. Garcia	June 2, 2001

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